DERWENT-ACC-NO: 2002-239657

DERWENT-WEEK: 200616

TITLE: Semiconductor device forming an insulating layer buried on the SOI substrate

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PATENT-FAMILY:

PUB-NO	PUB-DATE	LANGUAGE	PAGES	MAIN-IPC
US 7005755 B2	February 28, 2006	N/A	000	H01L 023/544
WO 200167509 A1	September 13, 2001	J	051	H01L 021/70
US 20030008472 A1	January 9, 2003	N/A	000	H01L 021/76
KR 2002077936 A	October 14, 2002	N/A	000	H01L 021/027
JP 2001566184 X	September 16, 2003	N/A	000	H01L 021/027
US 6706610 B2	March 16, 2004	N/A	000	H01L 021/76
US 20040135226 A1	July 15, 2004	N/A	000	H01L 021/76

DESIGNATED-STATES: JP KR US

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US 7005755B2	Cont of	2000WO-JP01435	March 9, 2000
US 7005755B2	Div ex	2002US-0231046	August 30, 2002
US 7005755B2	N/A	2003US-0745645	December 29, 2003
US 7005755B2	Div ex	US 6706610	N/A
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ABSTRACTED-PUB-NO: WO 200167509A

BASIC-ABSTRACT:

NOVELTY - A semiconductor device formed on a SOI substrate includes isolation trenches formed in a first region and reaching an insulating layer buried in the SOI substrate, and alignment marks formed in a second region and consisting of grooves extending into a support substrate.

USE - Semiconductor device forming an insulating layer buried on the SOI substrate

CHOSEN-DRAWING: Dwg.2D/7

TITLE-TERMS: SEMICONDUCTOR DEVICE FORMING INSULATE LAYER BURY SOI SUBSTRATE

DERWENT-CLASS: P84 U11

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